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**REMARKS**

Applicants thank the Examiner for the telephone call on 4 March 2003 indicating that the Examiner's objections to the specification in the Office Action dated 18 November 2002 required further attention from the Applicants.

Accordingly, Applicants hereby submit this Supplemental Amendment which it is believed should overcome the Examiner's objections.

Applicants respectfully request that the Examiner allow claims 2-10, 14, 15 and 21-23, and pass the application to issue. In the event that there are any outstanding matters remaining in the present application, the Examiner is invited to contact Kenneth D. Springer (Reg. No. 39,843) at (703) 715-0870 to discuss these matters.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies to charge payment or credit any overpayment to Deposit Account No. 50-0238 for any additional fees required under 37 C.F.R. § 1.16 or under 37 C.F.R. § 1.17, particularly extension of time fees.

Respectfully submitted,

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Date: 5 March 2003

By: 

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**Version with Markings to Show Changes Made****In the specification:**

Paragraph beginning at line 22 of page 4 has been amended as follows:

[FIGS.] FIG. 3A [through 9B are] shows a cross-sectional [views] view along an x-axis of a semiconductor substrate illustrating a step of a first embodiment of a semiconductor device fabrication method [according to the present invention];

FIG. 3B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a step of a first embodiment of a semiconductor device fabrication method;

FIG. 4A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 4B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 5A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

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FIG. 5B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 6A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 6B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 7A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 7B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 8A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

FIG. 8B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method;

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FIG. 9A shows a cross-sectional view along an x-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method:

FIG. 9B shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a first embodiment of a semiconductor device fabrication method; and

Paragraph beginning at line 25 of page 4 has been amended as follows:

[FIGS.] FIG. 10 [through 16 are cross-sectional views] shows a plan view of a semiconductor substrate illustrating a step of a second embodiment of a semiconductor device fabrication method [according to the present invention];

FIG. 11 shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method;

FIG. 12 shows a plan view of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method;

FIG. 13 shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method;

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FIG. 14 shows a plan view of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method;

FIG. 15 shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method;

FIG. 16 shows a cross-sectional view along a y-axis of a semiconductor substrate illustrating a subsequent step of a second embodiment of a semiconductor device fabrication method.